40V COMPLEMENTARY NPN/PNP SMALL SIGNAL TRANSISTOR

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

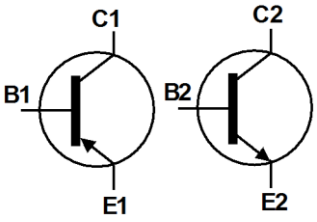
- BV_{CEO} >40V
- I_C = 600mA High Collector Current
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

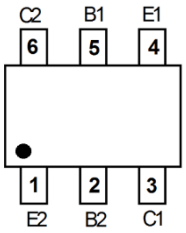
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Finish; Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

SOT363

Top View



Device Symbol



Top View
Pin-Out

Ordering Information (Note 5)

Product	Compliance	Marking	Reel Size (inch)	Tape Width (mm)	Quantity per Reel
MMDT2227Q-7-F	Automotive	K27	7	8	3,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

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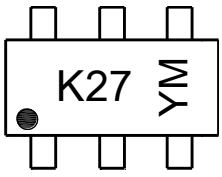

K27 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: E = 2017)
M or $\overline{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024
Code	E	F	G	H	I	J	K	L

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Absolute Maximum Ratings, NPN (2222A Type) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	600	mA

Absolute Maximum Ratings, PNP (2907A Type) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	625	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	150	°C/W
Operating and Storage and Temperature Range	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
6. For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
7. Thermal resistance from junction to the top of package.
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristic and Derating Information

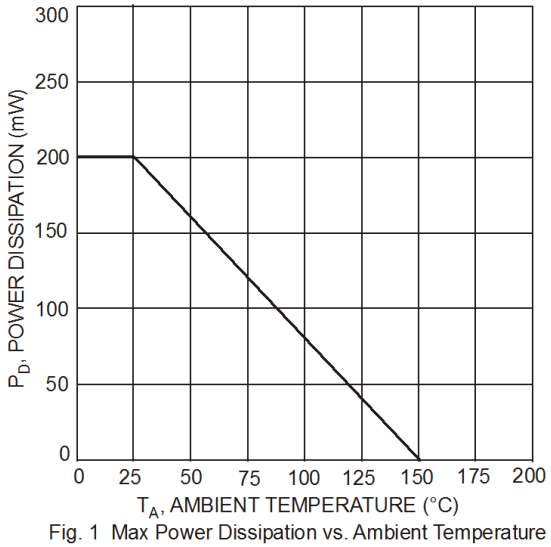

Fig. 1 Max Power Dissipation vs. Ambient Temperature

Electrical Characteristics, NPN (2222A Type) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_{CBO}	75	—	V	I_C = 100µA, I_E = 0
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	40	—	V	I_C = 10.0mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	—	V	I_E = 100µA, I_C = 0
Collector-Base Cut-Off Current	I_{CBO}	—	10	nA µA	V_{CB} = 60V, I_E = 0 V_{CB} = 60V, I_E = 0, T_A = +150°C
Collector-Emitter Cut-Off Current	I_{CEX}	—	10	nA	V_{CE} = 60V, $V_{EB(OFF)}$ = 3.0V
Emitter-Base Cut-Off Current	I_{EBO}	—	10	nA	V_{EB} = 5.0V, I_C = 0
Base Cut-Off Current	I_{BL}	—	20	nA	V_{CE} = 60V, $V_{EB(OFF)}$ = 3.0V
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h_{FE}	35 50 75 100 40 50 35	— — — 300 — — —	—	I_C = 100µA, V_{CE} = 10V I_C = 1.0mA, V_{CE} = 10V I_C = 10mA, V_{CE} = 10V I_C = 150mA, V_{CE} = 10V I_C = 500mA, V_{CE} = 10 I_C = 10mA, V_{CE} = 10V, T_A = -55°C I_C = 150mA, V_{CE} = 1.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.3 1.0	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.60 —	1.2 2.0	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	8	pF	V_{CB} =10V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	25	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = 20V, I_C = 20mA, f = 100MHz
Noise Figure	NF	—	4.0	dB	V_{CE} = 10V, I_C = 100µA, R_S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t_D	—	10	ns	V_{CC} = 30V, I_C = 150mA, $V_{BE(OFF)}$ = 0.5V, I_{B1} = 15mA
Rise Time	t_R	—	25	ns	
Storage Time	t_S	—	225	ns	V_{CC} = 30V, I_C = 150mA, I_{B1} =- I_{B2} = 15mA
Fall Time	t_F	—	60	ns	

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

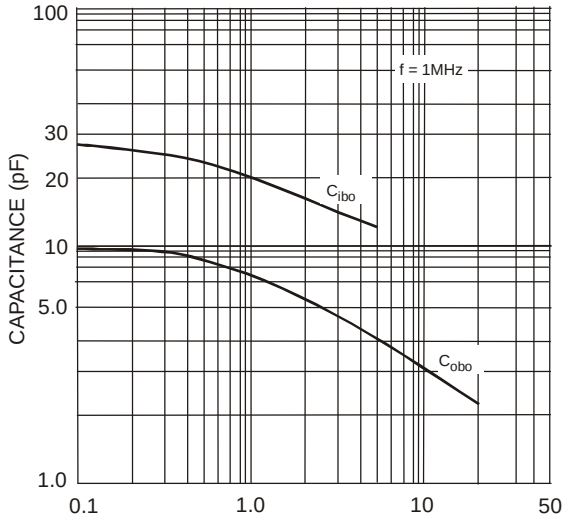

Fig. 1 (2222A) Typical Capacitance

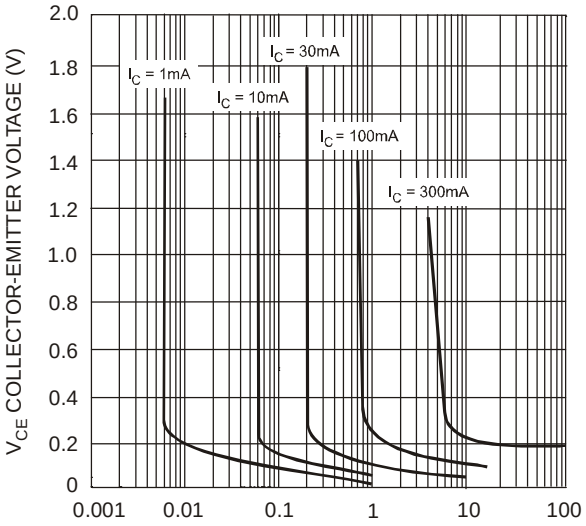

Fig. 2 Typical Collector Saturation Region (2222A Type - NPN)

Electrical Characteristics, PNP (2907A Type) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)					
Collector-Base Breakdown Voltage	BV_{CBO}	-60	—	V	I_C = -100μA, I_E = 0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-60	—	V	I_C = -10mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	-6.0	—	V	I_E = -100μA, I_C = 0
Collector Cutoff Current	I_{CBO}	—	-10	nA μA	V_{CB} = -50V, I_E = 0 V_{CB} = -50V, I_E = 0, T_A = +125°C
Collector Cutoff Current	I_{CEX}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -0.5V
Base Cutoff Current	I_{BL}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -0.5V
ON CHARACTERISTICS (Note 10)					
DC Current Gain	h_{FE}	75 100 100 100 50	— — — 300 —	—	I_C = -100μA, V_{CE} = -10V I_C = -1.0mA, V_{CE} = -10V I_C = -10mA, V_{CE} = -10V I_C = -150mA, V_{CE} = -10V I_C = -500mA, V_{CE} = -10V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.4 -1.6	V	I_C = -150mA, I_B = -15mA I_C = -500mA, I_B = -50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-1.3 -2.6	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	8.0	pF	V_{CB} = -10V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	30	pF	V_{EB} = -2.0V, f = 1.0MHz, I_C = 0
Current Gain-Bandwidth Product	f_T	200	—	MHz	V_{CE} = -20V, I_C = -50mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t_{ON}	—	45	ns	—
Delay Time	t_D	—	10	ns	V_{CC} = -30V, I_C = -150mA, I_{B1} = -15mA
Rise Time	t_R	—	40	ns	
Turn-Off Time	t_{OFF}	—	100	ns	—
Storage Time	t_S	—	80	ns	V_{CC} = -6.0V, I_C = -150mA, I_{B1} = -I_{B2} = -15mA
Fall Time	t_F	—	30	ns	

Notes: 10. Short duration pulse test used to minimize self-heating effect.

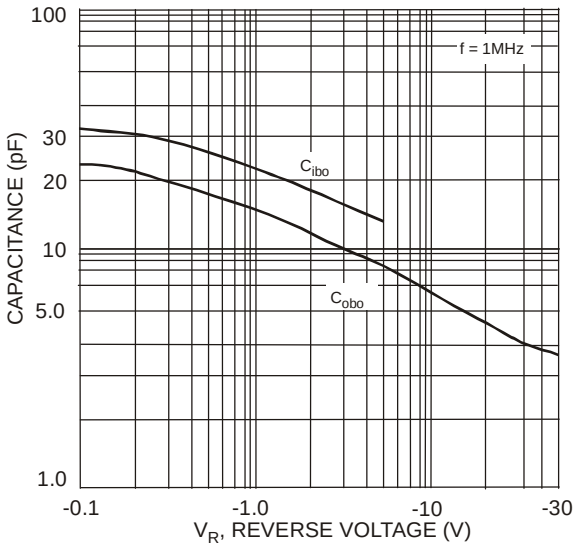

Fig. 3 (2907A) Typical Capacitance

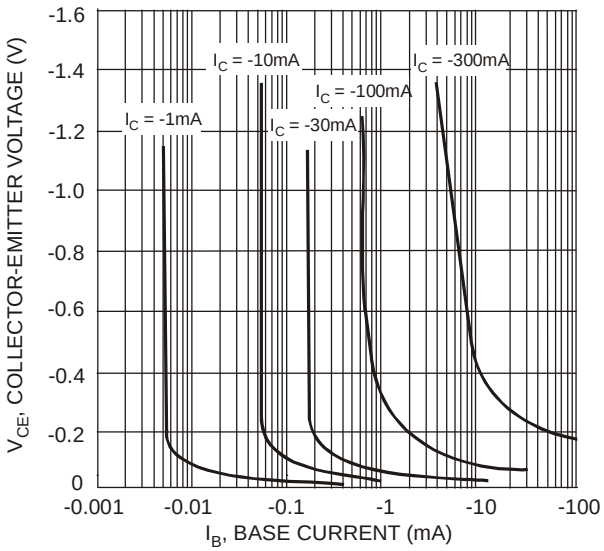

Fig. 4 Typical Collector Saturation Region (2907A Type - PNP)

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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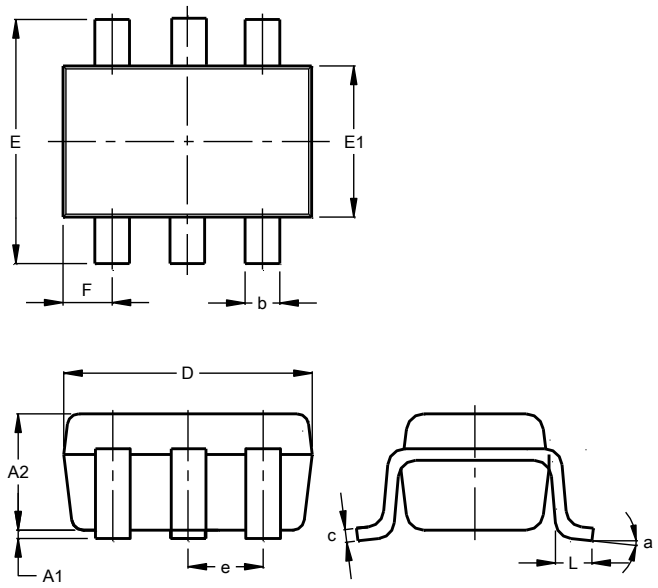

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Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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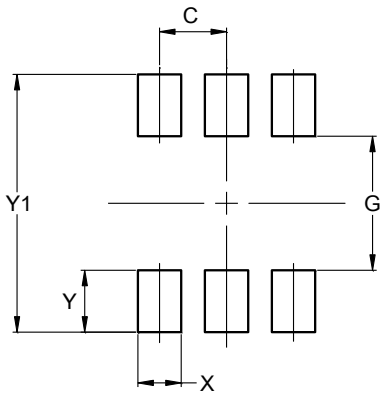

Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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